

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of :

Knut BEEKMAN et al. :

Serial No. [NEW] :

Filed: September 4, 2003 :

For: A METHOD OF DEPOSITING A LAYER

**INFORMATION DISCLOSURE STATEMENT  
(SUBMISSION IN CONTINUATION-IN-PART OR  
RULE 1.53(b) CONTINUATION OR DIVISIONAL APPLICATION)**

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Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, applicant(s) hereby submit(s) an Information Disclosure Statement for consideration by the Examiner.

**I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION**

The patents, publications or other information submitted for consideration by the Office are listed on PTO-1449 form(s), attached hereto.

**II. REFERENCES PREVIOUSLY CITED OR SUBMITTED**

Pursuant to 37 C.F.R. § 1.98(d), consideration of information listed on the PTO-1449 form(s) is requested since any patents, publications or other information which are listed on the PTO-1449 form(s) but for which copies are not enclosed herewith, were previously cited by or submitted to the PTO in one of the following applications which has been relied upon for an earlier filing date under 35 U.S.C. § 120:

U.S. Serial Number  
09/548,014

U.S. Filing Date  
April 12, 2000

III. FEES

This Information Disclosure Statement is being filed within three (3) months of the filing of the present application and/or prior to the issuance of a first action on the merits; therefore, no fee is required.

If the Examiner has any questions concerning this IDS or requires a copy of any of the references cited but not provided, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 50-0238.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 50-0238 for any additional fee required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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Dated: September 4, 2003

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.  
WLJ.051D

SERIAL NO.  
NEW

Knut Beekman et al.

FILING  
September 4, 2003

GROUP  
TO BE ASSIGNED

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A	5,242,860	09/1993	NULMAN et al.			
	B	5,523,259	06/1996	MERCHANT et al.			
	C	5,278,448	01/1994	FUJII			
	D	5,843,843	12/1998	LEE et al.			
	E	5,462,890	10/1995	HWANG et al.			
	F	6,143,128	11/2000	AMEEN et al.			
	G	5,204,192	03/2001	ZHAO et al.			
	H	6,077,571	06/2000	KALOYEROS et al.			
	I	5,899,720	05/1999	MIKAGI			
	J	5,591,663	01/1997	NASU et al.			
	K	5,851,917	12/1998	LEE			

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	L	11040518	02/1999	JAPAN				
	M	8274076	10/1996	JAPAN				
	N	7142412	06/1995	JAPAN				
	O	JP-9246212-A	09/1997	JAPAN				
	P	WO 88/02033	03/1998	PCT				

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Q	C.R. Aita, "Basal orientation aluminum nitride grown...", J. Appl. Phys. 53(3), March 1982, pages 1807-1808.
	R	Hwan-Chul Lee et al., "Effects of sputtering pressure and nitrogen concentration on the preferred orientation of AlN thin films," Journal of Materials Science: Materials in Electronics (1994) 221-225.

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. <b>WLJ.051D</b>		SERIAL NO. <b>NEW</b>	
				Knut Beekman et al.			
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<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	S	H1792-B2	04/1999	MORAN et al.			
	T	4,959,136	09/1990	HATWAR			
	U	4,957,604	09/1990	STEININGER			
	V	6,001,736	12/1999	KONDO et al.			
	W	5,795,823	08/1998	AVANZINO et al.			
	X	6,025,762	02/2000	ROY et al.			
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES      NO
	Y	0 327 888 A2	08/1989	EPO			
	Z	0 583 736 A1	02/1994	EPO			
	AA	2 266 897 A	11/1993	UK			
<b>OTHER DOCUMENTS    (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
		BB	Hiroshi Okano et al., "Preparation of C-Axis Oriented AlN Thin Films by Low-Temperature Reactive Sputtering, " Jpn. J. Appl. Phys. Vol. 31 (1992), Pt. 1, No. 10, pages 3446-3451.				
EXAMINER				DATE CONSIDERED			

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